

Diode

Emitter Controlled 4 Medium Power Technology
IDC10D120T8M

Data Sheet

Industrial Power Control



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Diode Chip in Emitter Controlled 4 Medium Power Technology

Features:

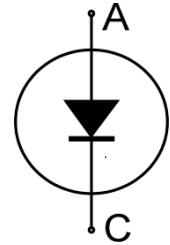
- 1200V Emitter Controlled 4 technology
110µm chip
- Soft, fast switching
- Low reverse recovery charge
- Small temperature coefficient

Recommended for:

- Low / medium power modules

Applications:

- Low / medium power drives



Chip Type	V_R	I_{FN}	Die Size	Package
IDC10D120T8M	1200V	15A	3.30mm x 2.98mm	Sawn on foil

Mechanical Parameters

Die size	3.30 x 2.98		mm ²
Area total	9.83		
Anode pad size	See chip drawing		
Silicon thickness	110		µm
Wafer size	200		mm
Maximum possible chips per wafer	2818		
Passivation frontside	Photoimide		
Pad metal	3.2µm AlSiCu		
Backside metal	Ni Ag – system To achieve a reliable solder connection it is strongly recommended not to consume the Ni layer completely during production process		
Die bond	Electrically conductive epoxy glue and soft solder		
Wire bond	Al, ≤500µm		
Reject ink dot size (valid for inked delivery form only)	Ø 0.65mm; max 1.2mm		
Storage environment (<12 months)	for original and sealed MBB bags	Ambient atmosphere air, temperature 17°C – 25°C	
	for open MBB bags	Acc. IEC 62258-3; Section 9.4 Storage Environment.	

Maximum Ratings

In general, from reliability and lifetime point of view, the lower the operation junction temperature and/or the applied voltage, the greater the expected lifetime of any semiconductor device.

Not subject to production test, specified by design.

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage, $T_{vj}=25^{\circ}\text{C}$	V_{RRM}	1200	V
Continuous forward current, limited by $T_{vj\ max}^1$	I_F	-	A
Maximum repetitive forward current, t_p limited by $T_{vj\ max}$	I_{FRM}	30	
Junction temperature	T_{vj}	-40...+175	$^{\circ}\text{C}$
Operating junction temperature	$T_{vj\ op}$	-40...+150	$^{\circ}\text{C}$

Static Characteristics (tested on wafer), $T_{vj}=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Reverse leakage current	I_R	$V_R=1200\text{V}$	-	-	3.5	μA
Cathode-anode breakdown voltage	V_{BR}	$I_R=0.25\text{mA}$	1200	-	-	V
Forward voltage drop	V_F	$I_F=15\text{A}$	1.35	1.70	2.05	

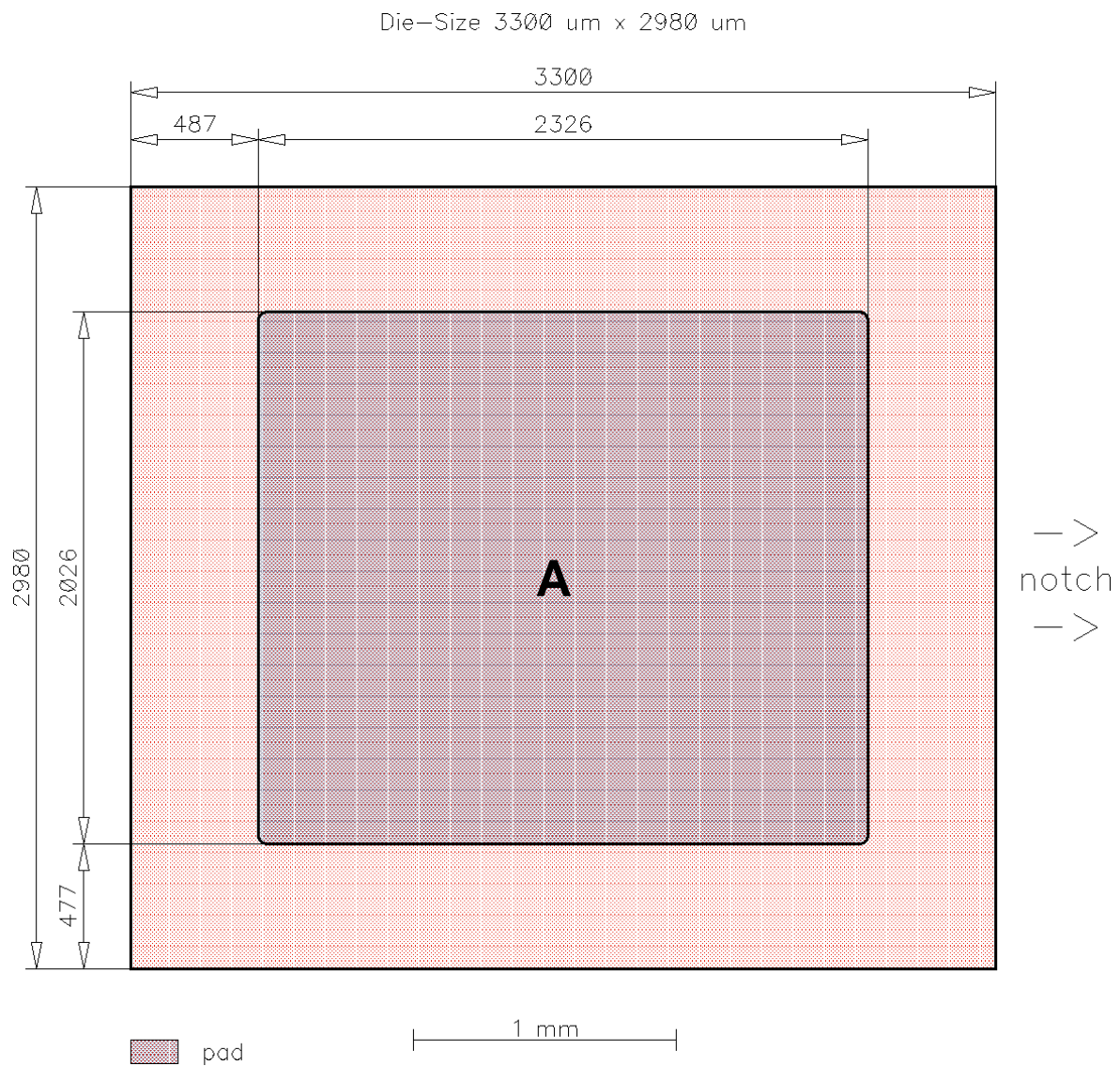
Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

Application example	F3L15R12W2H3_B27	Rev. 2.0
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¹ Depending on thermal properties of assembly.

Chip Drawing



A = Anode pad



IDC10D120T8M

Bare Die Product Specifics

Test coverage at wafer level cannot cover all application conditions. Therefore it is recommended to test all characteristics which are relevant for the application at package level, including RBSOA and SCSOA.

Description

AQL 0.65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Revision	Subjects (major changes since last revision)	Date
2.0	Final data sheet	22.08.2016
2.1	Editorial changes	09.04.2021



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